MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM6J424TU

#### 1. Applications

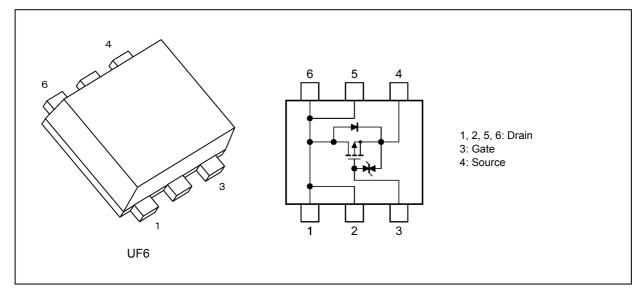
Power Management Switches

#### 2. Features

- (1) AEC-Q101 qualified (Note 1)
- (2) 1.5-V gate drive voltage.
- (3) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 54 \text{ m}\Omega \text{ (max)} (@V_{GS} = -1.5 \text{ V})$ 
    - $R_{DS(ON)} = 36 \text{ m}\Omega \text{ (max)} (@V_{GS} = -1.8 \text{ V})$
    - $R_{DS(ON)} = 26 \text{ m}\Omega \text{ (max)} (@V_{GS} = -2.5 \text{ V})$
    - $R_{DS(ON)} = 22.5 \text{ m}\Omega \text{ (max)} (@V_{GS} = -4.5 \text{ V})$

Note 1: For detail information, please contact to our sales.

#### 3. Packaging and Pin Configuration



#### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25^{\circ}$ C)

Characteristics			Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	-20	V	
Gate-source voltage		V <sub>GSS</sub>	-8/+6		
Drain current (DC)		۱ <sub>D</sub>	-6	A	
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	-14		
Power dissipation	(Note 2)	PD	1	W	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature		T <sub>stg</sub>	-55 to 150		

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1%

Note 2: Device mounted on an FR4 board.(25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu Pad: 645 mm²)

- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Electrical Characteristics

#### 5.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = -8/+6 V, V <sub>DS</sub> = 0 V	_	_	±1	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V		_	-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-20	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 5 V	-15		_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = -3 V, I <sub>D</sub> = -1 mA	-0.3	_	-1.0	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	$I_{\rm D}$ = -6.0 A, $V_{\rm GS}$ = -4.5 V	_	18	22.5	mΩ
			I <sub>D</sub> = -5.5 A, V <sub>GS</sub> = -2.5 V		21	26	
			I <sub>D</sub> = -3.0 A, V <sub>GS</sub> = -1.8 V		25	36	
			I <sub>D</sub> = -1.5 A, V <sub>GS</sub> = -1.5 V		29	54	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = -3 V, I <sub>D</sub> = -2.0 A	9.1	18.2	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

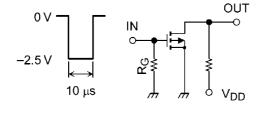
Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V,	_	1650	—	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz		90		
Output capacitance	C <sub>oss</sub>			220		
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -2.0 A V <sub>GS</sub> = 0 to -2.5 V, R <sub>G</sub> = 4.7 Ω,		77		ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1%, Input: t <sub>r</sub> , t <sub>f</sub> < 5 ns Common source, See Chapter 5.3		206		

#### 5.3. Switching Time Test Circuit



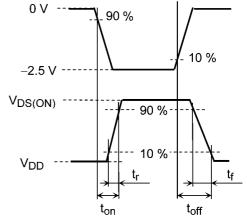


Fig. 5.3.1 Test Circuit of Switching Time

Fig. 5.3.2 Input Waveform/Output Waveform

#### 5.4. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = -10 V, V <sub>GS</sub> = -4.5 V,	—	23.1		nC
Gate-source charge 1	Q <sub>gs1</sub>	I <sub>D</sub> = -6.0 A	_	3.8	_	
Gate-drain charge	Q <sub>gd</sub>		_	4.1	_	

#### 5.5. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V <sub>DSF</sub>	I <sub>D</sub> = 6.0 A, V <sub>GS</sub> = 0 V	—	0.74	1.2	V

Note 1: Pulse measurement.

#### 6. Marking

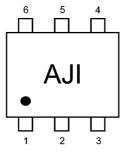
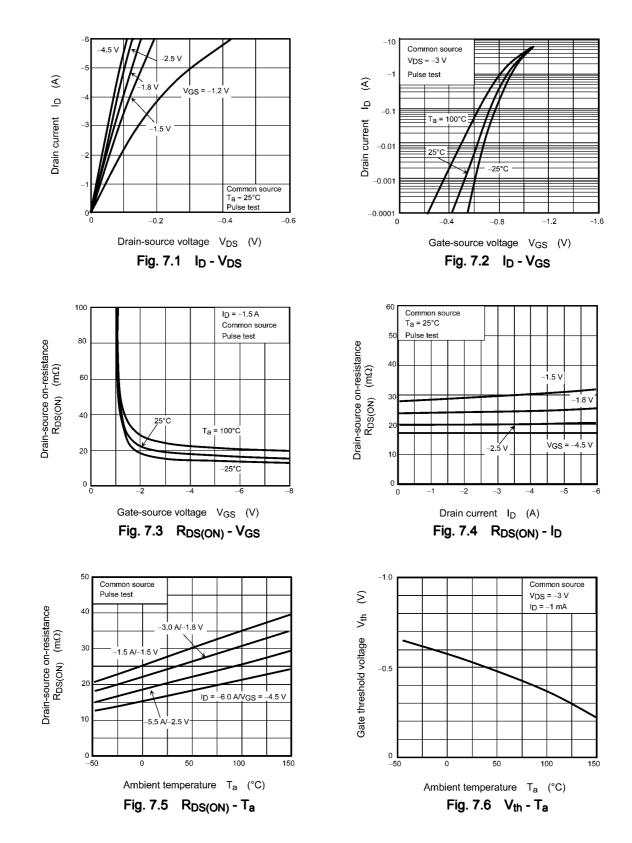


Fig. 6.1 Marking

#### 7. Characteristics Curves (Note)



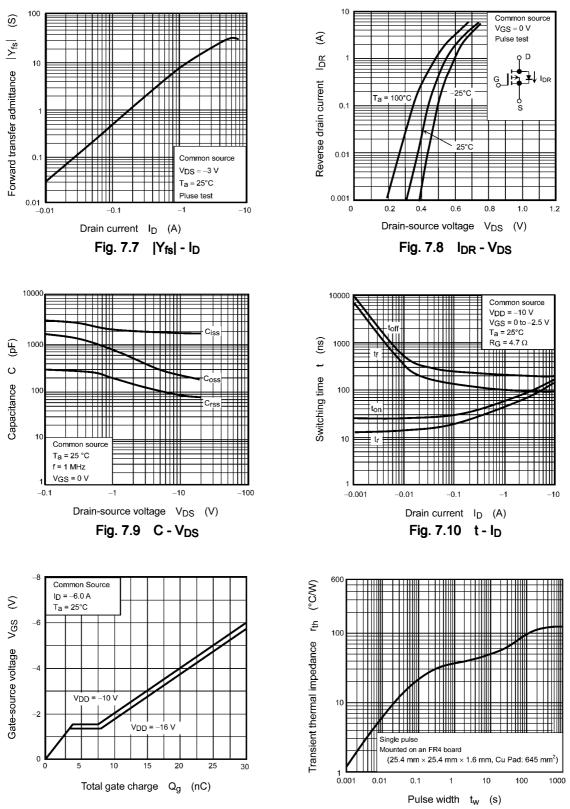
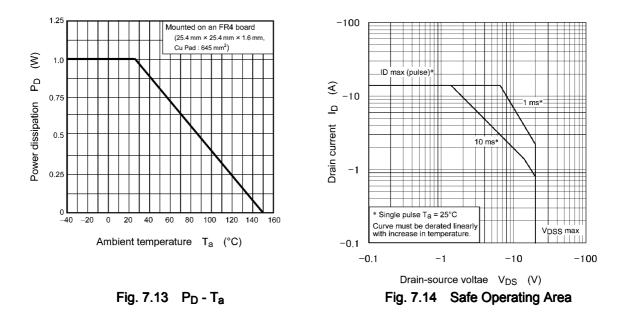


Fig. 7.11 Dynamic Input/Output Characteristics

Fig. 7.12 rth - tw

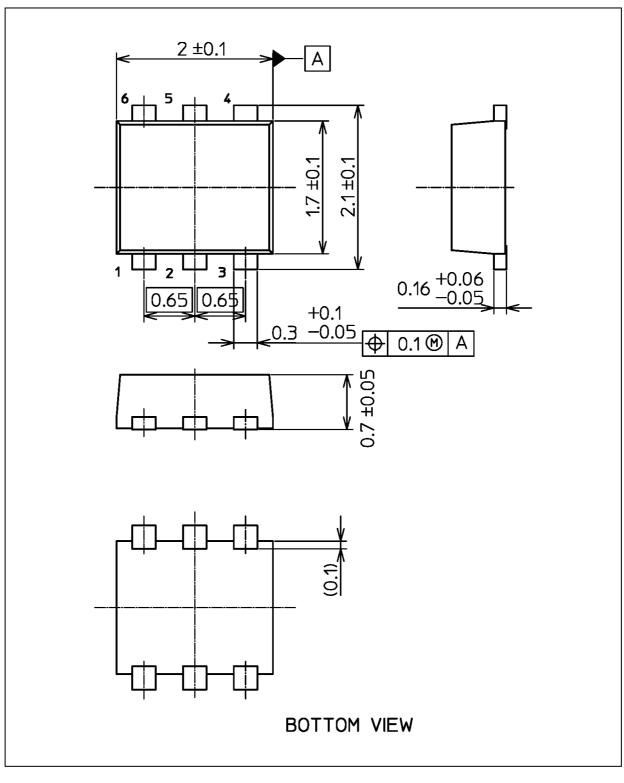


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



#### **Package Dimensions**

Unit: mm



Weight: 7.0 mg (typ.)

Package Name(s)

TOSHIBA: 2-2T1S

Nickname: UF6

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